



2N7002C

N-Channel Enhancement Mode Field Effect Transistor

Product Summary

V_{DS}	60V
I_D	350mA
$R_{DS(ON)}$ (at $V_{GS}=10V$)	1.0
$R_{DS(ON)}$ (at $V_{GS}=4.5V$)	1.4

General Description

Trench Power MV MOSFET technology
Voltage controlled small signal switch
Low input Capacitance
Fast Switching Speed
Low Input / Output Leakage
Moisture Sensitivity Level 1
Epoxy Meets UL 94 V-0 Flammability Rating
Halogen Free

Applications

Battery operated systems
Solid-state relays
Direct logic-level interface TTL/CMOS

Absolute Maximum Ratings ($T_A=25$ unless otherwise noted)

Parameter	Symbol	Limit	Unit
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Drain-



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Electrical Characteristics ($T_J=25$ unless otherwise noted)

Parameter	Symbol	Conditions	Min	Typ	Max	Units
Static Parameter						
Drain-Source Breakdown Voltage	BV_{DSS}	$V_{GS}=0V, I_D \leq I_{DM}$	60	-	-	V

Zero Gate Voltage Header*193.25 759.1 50.1





Figure 13. Maximum Transient Thermal Impedance

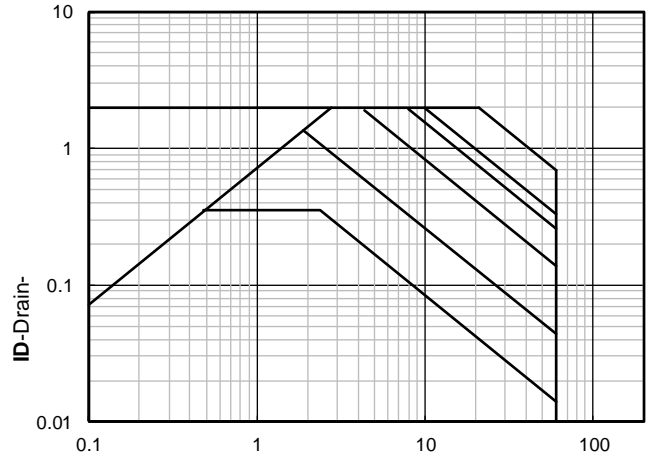


Figure 14. Safe Operation Area

Test Circuits & Waveforms

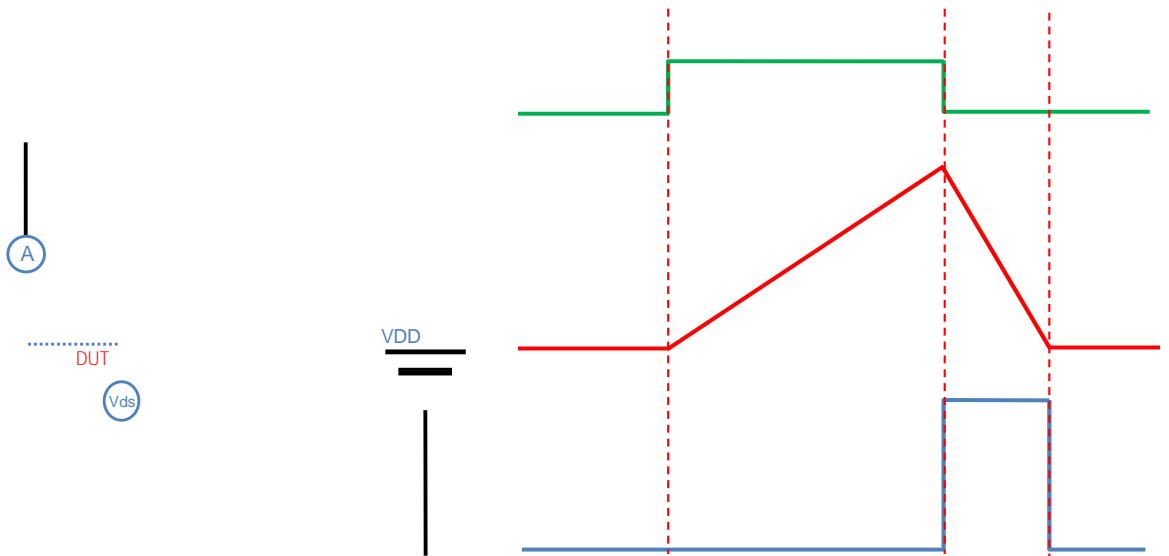
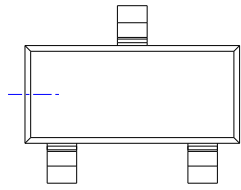


Figure A. Unclamped Inductive Switching (UIS) Test Circuit & Waveform

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SOT-23 Package information



UNIT: mm

